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Team Nexperia



9 July 2013

30 V; 1 A PNP low VCEsat (BISS) transistor

Product data sheet

### 1. General description

PNP low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a small SOT23 Surface-Mounted Device (SMD) plastic package.

### 2. Features and benefits

- Small SMD plastic package
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability:  $I_C$  and  $I_{CM}$
- Higher efficiency due to less heat generation
- AEC-Q101 qualified

### 3. Applications

- DC-to-DC conversion
- Supply line switching
- Battery charger
- LCD backlighting
- Driver in low supply voltage applications (e.g. lamps and LEDs)

### 4. Quick reference data

Table 1. Qu	ick reference data					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-30	V
I <sub>C</sub>	collector current		-	-	-1	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	-3	А
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C}$ = -500 mA; $I_{B}$ = -50 mA; pulsed; $t_{p} \le 300$ μs; δ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	-	220	mΩ





30 V; 1 A PNP low VCEsat (BISS) transistor

### 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	C L
2	E	emitter		в
3	С	collector		۲۳ 
			TO-236AB (SOT23)	E sym132

### 6. Ordering information

Table 3. Ordering in	formation			
Type number Package				
	Name	Description	Version	
PBSS5130T	TO-236AB	plastic surface-mounted package; 3 leads	SOT23	

### 7. Marking

Table 4. Marking codes	
Type number	Marking code
	[1]
PBSS5130T	%3E

[1] % = placeholder for manufacturing site code

30 V; 1 A PNP low VCEsat (BISS) transistor

### 8. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-30	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-30	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-5	V
I <sub>C</sub>	collector current			-	-1	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-3	А
I <sub>BM</sub>	peak base current	_		-	-300	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	300	mW
			[2]	-	480	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

### 9. Thermal characteristics

Table 6. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1]	-	-	417	K/W
	from junction to ambient		[2]	-	-	260	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

30 V; 1 A PNP low VCEsat (BISS) transistor

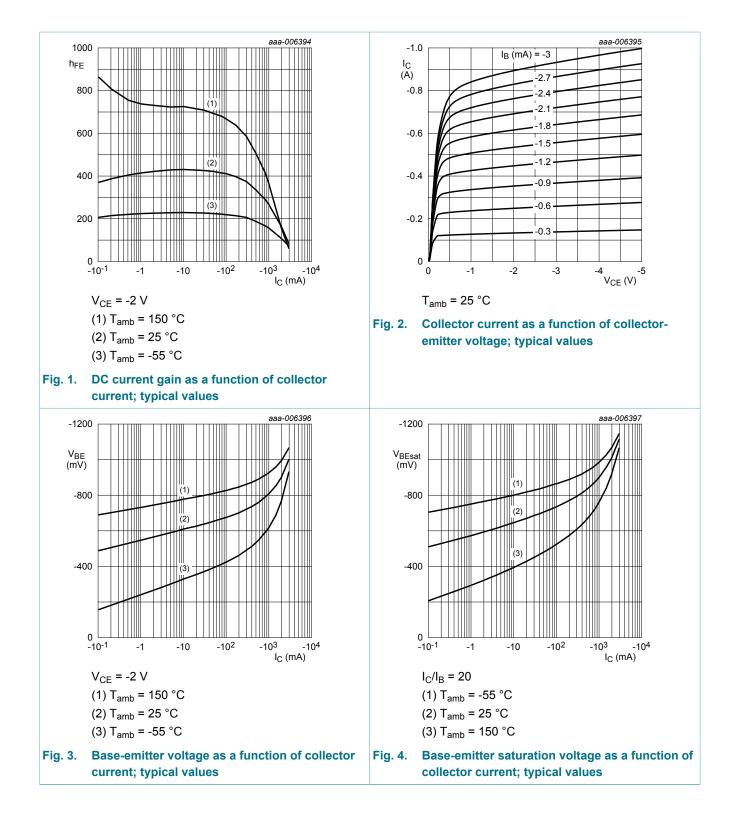
### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = -30 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	V <sub>CB</sub> = -30 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB}$ = -4 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -2 V; I <sub>C</sub> = -100 mA; pulsed; t <sub>p</sub> ≤ 300 µs; $\delta$ ≤ 0.02 ; T <sub>amb</sub> = 25 °C	300	450	-	
		$V_{CE}$ = -2 V; I <sub>C</sub> = -500 mA; pulsed; t <sub>p</sub> ≤ 300 µs; $\delta$ ≤ 0.02 ; T <sub>amb</sub> = 25 °C	260	350	-	
		$V_{CE}$ = -2 V; I <sub>C</sub> = -1 A; pulsed; t <sub>p</sub> ≤ 300 µs; $\overline{\delta}$ ≤ 0.02 ; T <sub>amb</sub> = 25 °C	210	290	-	
OLGUI	collector-emitter saturation voltage	$I_{C}$ = -100 mA; $I_{B}$ = -1 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	-	-100	mV
		$I_{C}$ = -1 A; $I_{B}$ = -50 mA; pulsed; $t_{p} \le 300$ μs; δ $\le 0.02$ ; $T_{amb}$ = 25 °C	-	-	-225	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C}$ = -500 mA; $I_{B}$ = -50 mA; pulsed; $t_{p} \le 300$ μs; δ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	-	220	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = -2 A; I <sub>B</sub> = -200 mA; pulsed; t <sub>p</sub> ≤ 300 μs; $\delta$ ≤ 0.02 ; T <sub>amb</sub> = 25 °C	-	-	-1.1	V
V <sub>BEon</sub>	base-emitter turn-on voltage	$V_{CE}$ = -2 V; I <sub>C</sub> = -100 mA; pulsed; t <sub>p</sub> ≤ 300 µs; $\delta$ ≤ 0.02 ; T <sub>amb</sub> = 25 °C	-	-	-0.75	V
f <sub>T</sub>	transition frequency	V <sub>CE</sub> = -10 V; I <sub>C</sub> = -100 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	100	200	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	-	28	pF

#### **NXP Semiconductors**

### PBSS5130T

#### 30 V; 1 A PNP low VCEsat (BISS) transistor



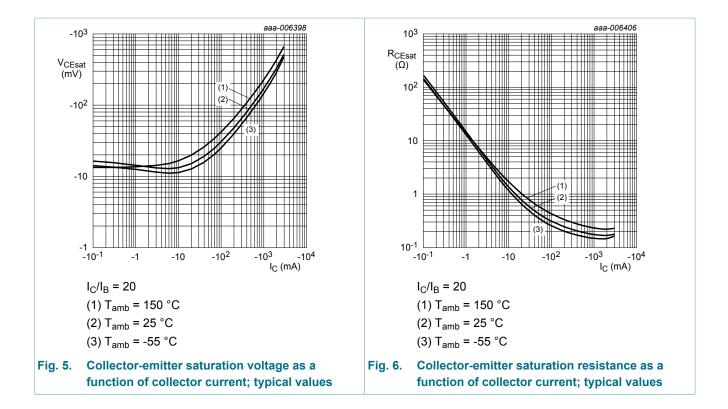
PBSS5130T

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### PBSS5130T

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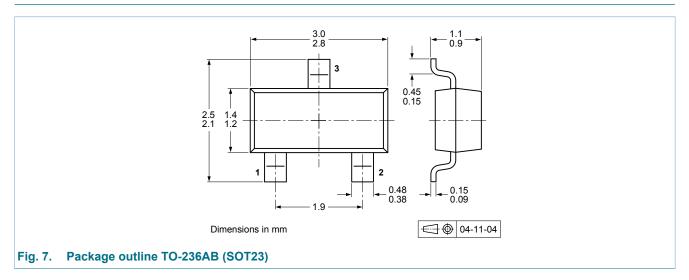


#### **11. Test information**

#### 11.1 Quality information

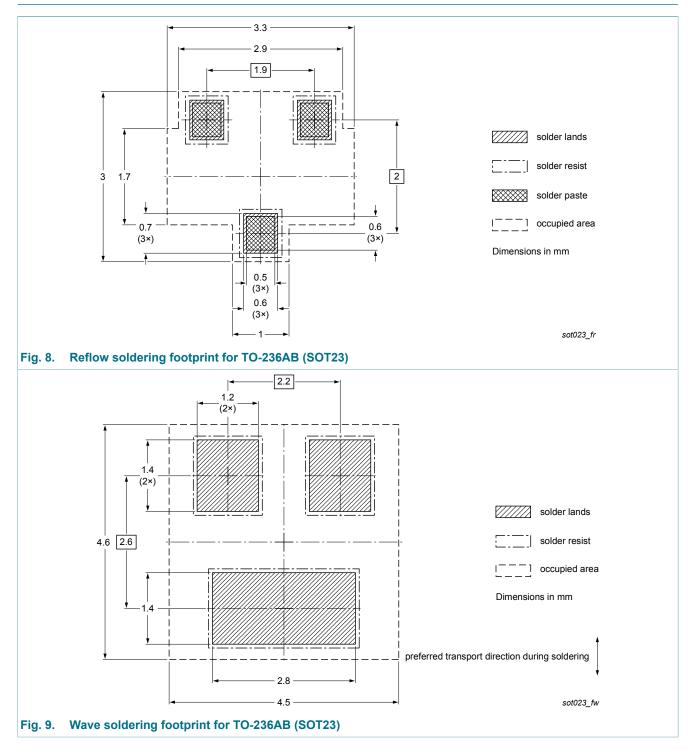
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

### 12. Package outline



#### 30 V; 1 A PNP low VCEsat (BISS) transistor

### 13. Soldering



30 V; 1 A PNP low VCEsat (BISS) transistor

### 14. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5130T v.2	20130709	Product data sheet	-	PBSS5130T v.1
Modifications:	of NXP Semicond Legal texts have b Sections "Genera Section "Marking" Table "Limiting va Table "Characteris Figures 1 to 6: ad Section "Test infor Figure "Package o Section "Soldering	been adapted to the new co I description", "Features an ': updated lues": ambient temperature stics": base-emitter saturat ded rmation": added putline TO-236AB (SOT23)	ompany name where app nd benefits" and "Applica e T <sub>amb</sub> updated ion voltage V <sub>BEsat</sub> added	propriate. tions": updated
PBSS5130T v.1	20031212	Product data sheet	-	-

#### 30 V; 1 A PNP low VCEsat (BISS) transistor

#### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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#### 30 V; 1 A PNP low VCEsat (BISS) transistor

#### 16. Contents

1	General description1
2	Features and benefits1
3	Applications1
4	Quick reference data1
5	Pinning information2
6	Ordering information2
7	Marking2
8	Limiting values3
9	Thermal characteristics3
10	Characteristics4
11	Test information6
11.1	Quality information6
12	Package outline6
13	Soldering7
14	Revision history8
15	Legal information9
15.1	Data sheet status9
15.2	Definitions9
15.3	Disclaimers9
15.4	Trademarks 10

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